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PATENT

Attorney Docket No. 5308

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Saxler et al.

Serial No.: 10/617,843

Filed: July 11, 2003

For: NITRIDE-BASED TRANSISTORS AND METHODS OF FABRICATION THEREOF
USING NON-ETCHED CONTACT RECESSES

Group Art Unit: 2823

Examiner: Fernando L. Toledo

Confirmation No.: 7985

Date: July 8, 2004

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

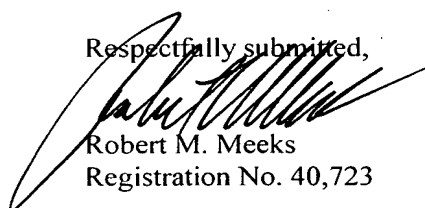
FIFTH INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97(b)

Sir:

Attached is a list of documents on Form PTO-1449, together with a copy of any listed foreign patent document and/or non-patent literature. A copy of any listed U.S. patent and/or U.S. patent application publication is not provided herewith in accordance with the waiver by the U.S. Patent and Trademark Office of requirements under 37 C.F.R. § 1.98(a)(2)(i) for all U.S. national patent applications filed after June 30, 2003 and for all international applications that have entered the national stage under 35 USC § 371 after June 30, 2003.

It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. § 1.56 and Section 609 of the MPEP. No fee is believed due. However, the Commissioner is hereby authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

Respectfully submitted,

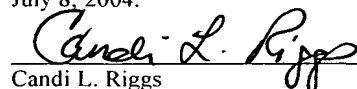


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FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office				Attorney Docket Number: 5308-248		Serial No.: 10/617,843	
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Applicants: Saxler et al.			
				Filing Date: July 11, 2003		Group: 2823	
U. S. PATENT DOCUMENTS							
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
	1.	6,586,781 B2	7/1/03	Wu et al.	257	194	
	2.	6,548,333 B2	4/15/03	Smith	438	172	
	3.	6,515,316 B1	2/4/03	Wojtowicz	257	194	
	4.	6,448,648 B1	9/10/02	Boos	257	751	
	5.	6,429,467 B1	8/6/02	Ando	257	194	
	6.	6,046,464	4/4/00	Schetzina	257	96	
	7.	6,028,328	2/22/00	Riechert et al.	257	194	
	8.	5,172,197	12/15/92	Nguyen et al.	357	22	
	9.	5,053,348	10/1/91	Mishra et al.	437	41	
	10.	4,946,547	8/7/90	Palmour et al.	156	643	
	11.	2004/0029330 A1	2/12/04	Hussain et al.	438	172	
	12.	2004/0021152 A1	2/5/04	Nguyen et al.	257	192	
	13.	2003/0102482 A1	6/5/03	Saxler	257	85	
	14.	2003/0020092 A1	1/30/03	Parikh et al.	257	192	
	15.	2002/0167023 A1	11/14/02	Chavarkar et al.	257	194	
	16.	2001/0023964 A1	09/27/01	Wu et al.	257	368	
	17.	2001/0020700 A1	09/13/01	Inoue et al.	257	20	
FOREIGN PATENT DOCUMENTS							
	Document Number	Date	Country	Class	Subclass	Translation Yes No	
	18.	WO 93/23877	11/25/93	PCT	H01L	29/10	
	19.	10-050982	2/20/98	JP	H01L	29/778	
	20.	0 563 847 A2	10/6/93	EP	H01L	29/812	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
	21.	Breitschadel et al., "Minimization of Leakage Current of Recessed Gate AlGaIn/GaN HEMTs by Optimizing the Dry-Etching Process", Journal of Electronic Materials, Volume 28, No. 12, 1999.					
	22.	Burm et al., "Recessed Gate GaN MODFETS", Solid State Electronics, Volume 41, No. 2, pp. 247-250, 1997					
	23.	Chen et al., "Reactive ion etching for gate recessing of AlGaIn/GaN Field-effect transistors", J. Vac. Sci. Technol. B 17(6), Nov/Dec 1999					

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Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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